21 September 2023

Product data sheet

1. General description

General purpose MOSFET for standard applications, 56 A, logic level N-channel enhancement mode Power MOSFET in MLPAK33 package.

2. Features and benefits

- · Logic level compatibility
- Trench MOSFET technology
- Thermally efficient package in a small form factor (3.3 mm x 3.3 mm footprint)

3. Applications

- · Secondary side synchronous rectification
- DC-to-DC converters
- · Home appliance
- · Motor drive
- · Load switching
- LED lighting

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	56	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	66	W
T _j	junction temperature			-55	-	150	°C
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 9$		-	8.3	11	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$		-	10.4	14	mΩ
Dynamic chara	acteristics			•	'		
Q_{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 50 V; V _{GS} = 4.5 V;		-	7.5	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>		-	18	-	nC
Avalanche rug	gedness		•				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 9.2 A; $V_{sup} \le 100$ V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[1]	-	-	168.9	mJ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
Q _r		$I_S = 10 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$	[2]	-	19	-	nC

- [1] Protected by 100% test
- [2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source	رث ث ث ث	
3	S	source		D ⊥
4	G	gate		
5	D	drain		G T A
6	D	drain	Lanal	mbb076 S
7	D	drain	8 7 6 5 MI DAK 22 (SOT 2002 4)	
8	D	drain	MLPAK33 (SOT8002-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PXN011-100QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1			

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN011-100QL	9AL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	100	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	66	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	56	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	35	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3	-	224	Α
T _{stg}	storage temperature		-55	150	°C

Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	150	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain	diode			•		<u>'</u>
Is	source current	T _{mb} = 25 °C		-	55	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	224	Α
Avalanche ru	ggedness			'	'	'
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 9.2 A; $V_{sup} \le 100 \text{ V}$; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[1]	-	168.9	mJ
I _{AS}	non-repetitive avalanche current	$T_{j(init)} = 25 ^{\circ}C$	[1]	-	9.2	Α

[1] Protected by 100% test

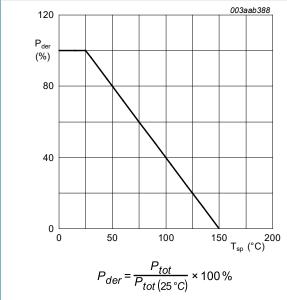


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

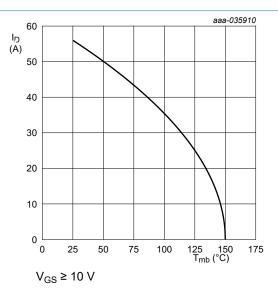
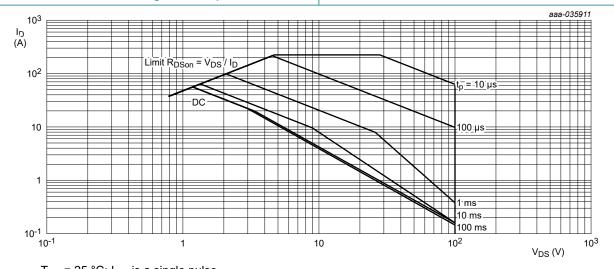


Fig. 2. Continuous drain current as a function of mounting base temperature



 T_{mb} = 25 °C; I_{DM} is a single pulse

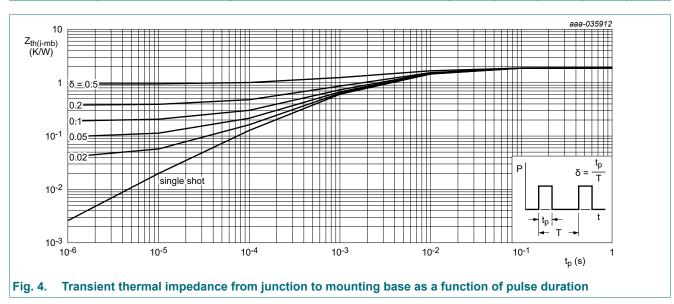
Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

N-channel 100 V, 11 mOhm, logic level Trench MOSFET in MLPAK33

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	1.57	1.89	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics		'			
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	-	100	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 8	1.2	1.53	2.2	V
		I _D = 0.25 mA; V _{DS} =V _{GS} ; T _j = 150 °C	-	0.8	-	V
		$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	1.9	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-6.1	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 150 °C	-	22	-	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 9</u>	-	8.3	11	mΩ
	resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 150 °C; Fig. 10	-	-	21	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$	-	10.4	14	mΩ
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 150 °C; Fig. 10	-	-	27	mΩ

Product data sheet

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _G	gate resistance	f = 1 MHz; T _j = 25 °C		-	1	-	Ω
Dynamic cl	haracteristics						
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 4.5 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 11}}; \underline{\text{Fig. 12}}$		-	18	-	nC
		I _D = 10 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>		-	35	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$		-	30	-	nC
Q _{GS}	gate-source charge	I _D = 10 A; V _{DS} = 50 V; V _{GS} = 4.5 V;		-	4.6	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 11; Fig. 12</u>		-	3	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge			-	1.6	-	nC
Q _{GD}	gate-drain charge			-	7.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 10 A; V_{DS} = 50 V; T_j = 25 °C; Fig. 11; Fig. 12		-	2.6	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;		-	1898	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>		-	567	-	pF
C _{rss}	reverse transfer capacitance			-	22	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 5 \Omega; V_{GS} = 4.5 \text{ V};$		-	13	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$		-	21	-	ns
t _{d(off)}	turn-off delay time			-	22	-	ns
t _f	fall time			-	18	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	42	-	nC
Source-dra	in diode			'		'	
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 14$		-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	29	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V; } T_j = 25 \text{ °C; } Fig. 15$	[1]	-	19	-	nC

^[1] includes capacitive recovery

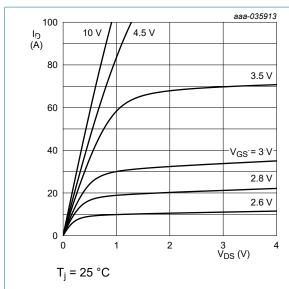


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

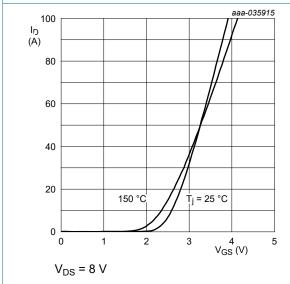


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

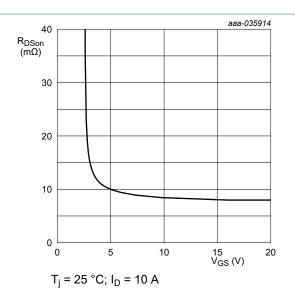


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

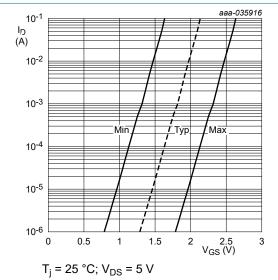


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

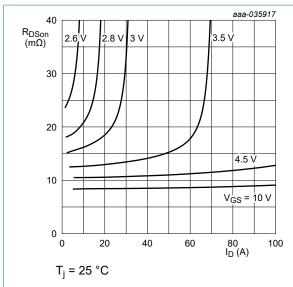


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

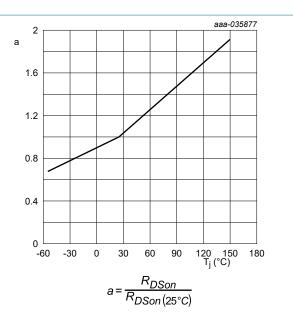


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

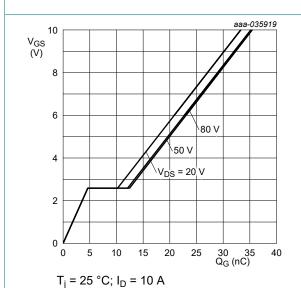


Fig. 11. Gate-source voltage as a function of gate charge; typical values

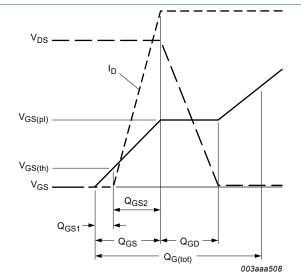


Fig. 12. Gate charge waveform definitions

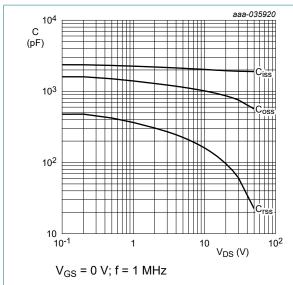
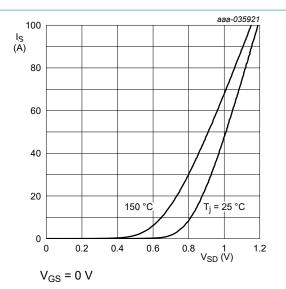


Fig. 13. Input, output and reverse transfer capacitances | Fig. 14. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

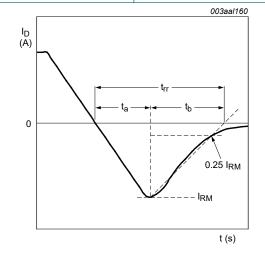
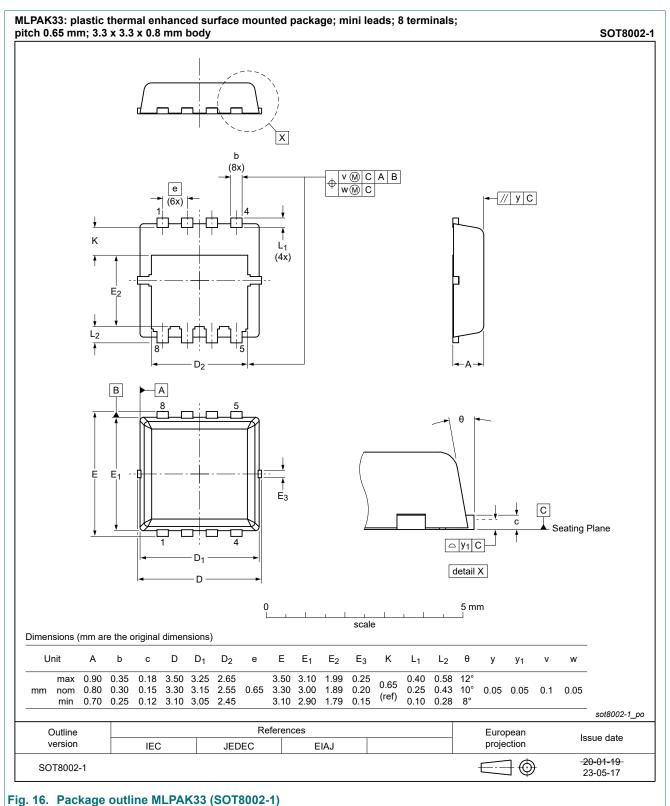


Fig. 15. Reverse recovery timing definition

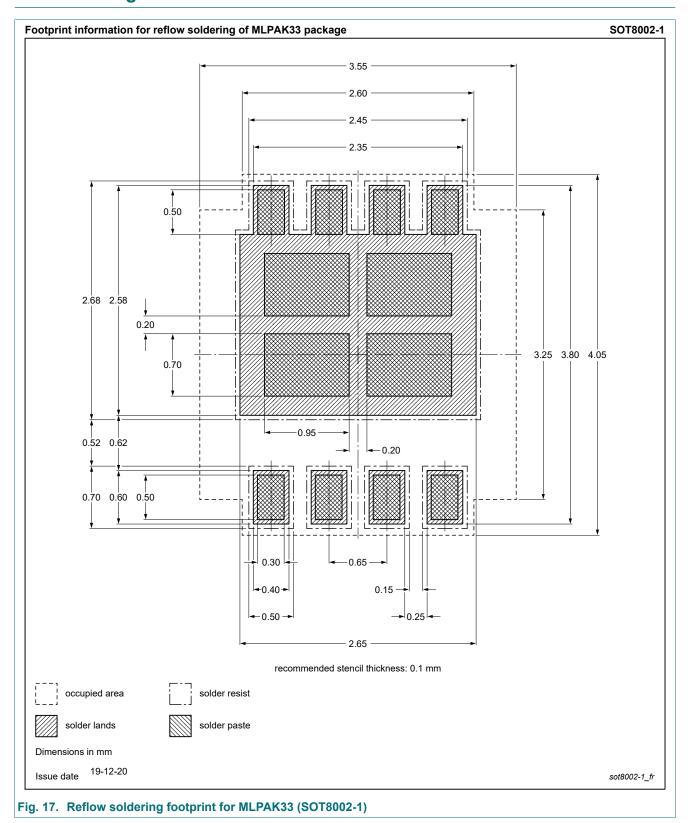
N-channel 100 V, 11 mOhm, logic level Trench MOSFET in MLPAK33

11. Package outline



N-channel 100 V, 11 mOhm, logic level Trench MOSFET in MLPAK33

12. Soldering



PXN011-100QL

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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